



### C2M0080120D Information



For Reference Only

Part Number C2M0080120D

Manufacturer Cree/Wolfspeed

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 1200V 31.6A TO247

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## **C2M0080120D Specifications**

Manufacturer Part Number         C2M0080120D           Manufacturer         Cree/Wolfspeed           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-247-3           Series         C2M?           FET Type         N-Channel           Technology         SiCFET (Silicon Carbide)           Drain to Source Voltage (Vdss)         1200V           Current - Continuous Drain (Id) @ 25°C         36A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         20V           Vgs(th) (Max) @ Id         4V @ 5mA           Gate Charge (Qg) (Max) @ Vgs         62nC @ 5V           Input Capacitance (Ciss) (Max) @ Vds         950pF @ 1000V           Vgs (Max)         +25V, -10V           FET Feature         -           Power Dissipation (Max)         192W (Tc)           Rds On (Max) @ Id, Vgs         98 mOhm @ 20A, 20V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-247-3           Package / Case         TO-247-3		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-247-3           Series         C2M?           FET Type         N-Channel           Technology         SiCFET (Silicon Carbide)           Drain to Source Voltage (Vdss)         1200V           Current - Continuous Drain (Id) @ 25°C         36A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         20V           Vgs(th) (Max) @ Id         4V @ 5mA           Gate Charge (Qg) (Max) @ Vgs         62nC @ 5V           Input Capacitance (Ciss) (Max) @ Vds         950pF @ 1000V           Vgs (Max)         +25V, -10V           FET Feature         -           Power Dissipation (Max)         192W (Tc)           Rds On (Max) @ Id, Vgs         98 mOhm @ 20A, 20V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-247-3           Package / Case         TO-247-3	Manufacturer Part Number	C2M0080120D
Package         TO-247-3           Series         C2M?           FET Type         N-Channel           Technology         SiCFET (Silicon Carbide)           Drain to Source Voltage (Vdss)         1200V           Current - Continuous Drain (Id) @ 25°C         36A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         20V           Vgs(th) (Max) @ Id         4V @ 5mA           Gate Charge (Qg) (Max) @ Vgs         62nC @ 5V           Input Capacitance (Ciss) (Max) @ Vds         950pF @ 1000V           Vgs (Max)         +25V, -10V           FET Feature         -           Power Dissipation (Max)         192W (Tc)           Rds On (Max) @ Id, Vgs         98 mOhm @ 20A, 20V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-247-3           Package / Case         TO-247-3	Manufacturer	Cree/Wolfspeed
PackageTO-247-3SeriesC2M?FET TypeN-ChannelTechnologySiCFET (Silicon Carbide)Drain to Source Voltage (Vdss)1200VCurrent - Continuous Drain (Id) @ 25°C36A (Tc)Drive Voltage (Max Rds On, Min Rds On)20VVgs(th) (Max) @ Id4V @ 5mAGate Charge (Qg) (Max) @ Vgs62nC @ 5VInput Capacitance (Ciss) (Max) @ Vds950pF @ 1000VVgs (Max)+25V, -10VFET Feature-Power Dissipation (Max)192W (Tc)Rds On (Max) @ Id, Vgs98 mOhm @ 20A, 20VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	Category	Discrete Semiconductor Products
Series         C2M?           FET Type         N-Channel           Technology         SiCFET (Silicon Carbide)           Drain to Source Voltage (Vdss)         1200V           Current - Continuous Drain (Id) @ 25°C         36A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         20V           Vgs(th) (Max) @ Id         4V @ 5mA           Gate Charge (Qg) (Max) @ Vgs         62nC @ 5V           Input Capacitance (Ciss) (Max) @ Vds         950pF @ 1000V           Vgs (Max)         +25V, -10V           FET Feature         -           Power Dissipation (Max)         192W (Tc)           Rds On (Max) @ Id, Vgs         98 mOhm @ 20A, 20V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-247-3           Package / Case         TO-247-3		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology SiCFET (Silicon Carbide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 36A (Tc) Drive Voltage (Max Rds On, Min Rds On) 20V Vgs(th) (Max) @ Id 4V @ 5mA Gate Charge (Qg) (Max) @ Vgs 62nC 5V Input Capacitance (Ciss) (Max) @ Vds 950pF @ 1000V Vgs (Max) +25V, -10V FET Feature Power Dissipation (Max) 192W (Tc) Rds On (Max) @ Id, Vgs 98 mOhm @ 20A, 20V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 70-247-3 Package / Case 7100 Trained Temperature 70-247-3	Package	TO-247-3
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  36A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  Ygs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-247-3  Package / Case  TO-247-3  Table V  36A (Tc)  4V @ 5mA  4v @ 5mA	Series	C2M?
Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  36A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  4V @ 5mA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Poperating Temperature  Supplier Device Package  Package / Case  1200V  36A (Tc)  4V @ 5mA  4V @ 5m	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  20V  Vgs(th) (Max) @ Id  4V @ 5mA  Gate Charge (Qg) (Max) @ Vgs  62nC @ 5V  Input Capacitance (Ciss) (Max) @ Vds  950pF @ 1000V  Vgs (Max)  +25V, -10V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  98 mOhm @ 20A, 20V  Operating Temperature  4-55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-247-3  Package / Case  36A (Tc)  4V @ 5mA  4V @ 5mA  950pF @ 1000V  950pF @ 1000V  1	Technology	SiCFET (Silicon Carbide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  4V @ 5mA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  Pockage / Case  TO-247-3	Drain to Source Voltage (Vdss)	1200V
Vgs(th) (Max) @ Id       4V @ 5mA         Gate Charge (Qg) (Max) @ Vgs       62nC @ 5V         Input Capacitance (Ciss) (Max) @ Vds       950pF @ 1000V         Vgs (Max)       +25V, -10V         FET Feature       -         Power Dissipation (Max)       192W (Tc)         Rds On (Max) @ Id, Vgs       98 mOhm @ 20A, 20V         Operating Temperature       -55°C ~ 150°C (TJ)         Mounting Type       Through Hole         Supplier Device Package       TO-247-3         Package / Case       TO-247-3	Current - Continuous Drain (Id) @ 25°C	36A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  950pF @ 1000V  Vgs (Max)  +25V, -10V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  98 mOhm @ 20A, 20V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-247-3  Package / Case  TO-247-3	Drive Voltage (Max Rds On, Min Rds On)	20V
Input Capacitance (Ciss) (Max) @ Vds  950pF @ 1000V  Vgs (Max)  +25V, -10V  FET Feature  - Power Dissipation (Max)  192W (Tc)  Rds On (Max) @ Id, Vgs  98 mOhm @ 20A, 20V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-247-3  Package / Case  TO-247-3	Vgs(th) (Max) @ Id	4V @ 5mA
Vgs (Max) +25V, -10V  FET Feature -  Power Dissipation (Max) 192W (Tc)  Rds On (Max) @ Id, Vgs 98 mOhm @ 20A, 20V  Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-247-3  Package / Case TO-247-3	Gate Charge (Qg) (Max) @ Vgs	62nC @ 5V
FET Feature - Power Dissipation (Max) 192W (Tc) Rds On (Max) @ Id, Vgs 98 mOhm @ 20A, 20V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Input Capacitance (Ciss) (Max) @ Vds	950pF @ 1000V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  98 mOhm @ 20A, 20V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-247-3  Package / Case  TO-247-3	Vgs (Max)	+25V, -10V
Rds On (Max) @ Id, Vgs98 mOhm @ 20A, 20VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-247-3  Package / Case TO-247-3	Power Dissipation (Max)	192W (Tc)
Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	98 mOhm @ 20A, 20V
Supplier Device Package TO-247-3 Package / Case TO-247-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	TO-247-3
Report errors?	Package / Case	TO-247-3
		Report errors?

#### C2M0080120D Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### C2M0080120D Payment Methods



















### **C2M0080120D Shipping Methods**













If you have any question about C2M0080120D, please do not hesitate to contact us!

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